

## RJL5018DPK

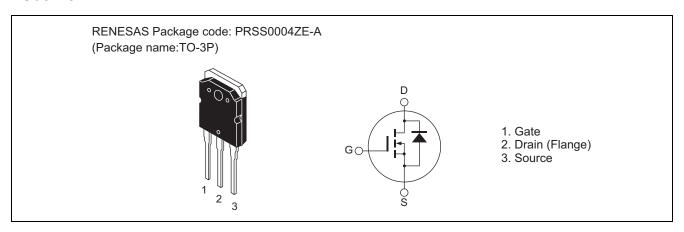
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1817-0100 Rev.1.00 Sep 11, 2009

#### **Features**

- Built-in fast recovery diode
- Low on-resistance
- Low leakage current
- High speed switching

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	500	V
Gate to source voltage	$V_{GSS}$	±30	V
Drain current	I <sub>D</sub>	35	А
Drain peak current	I <sub>D (pulse)</sub> Note1	105	Α
Body-drain diode reverse drain current	I <sub>DR</sub>	35	А
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	105	А
Avalanche current	I <sub>AP</sub> Note3	9	А
Avalanche energy	E <sub>AR</sub> Note3	4.5	mJ
Channel dissipation	Pch Note2	200	W
Channel to case thermal impedance	θch-c	0.625	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

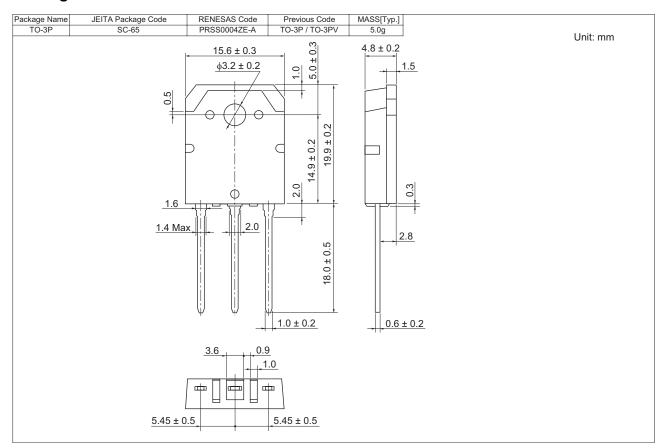
#### **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	10	μА	$V_{DS} = 500 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μА	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	_	4.0	V	$V_{DS}$ = 10 V, $I_{D}$ = 1 mA
Static drain to source on state resistance	R <sub>DS(on)</sub>	1	0.14	0.17	Ω	$I_D = 17.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss		3790	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	410	_	pF	V <sub>GS</sub> = 0
Reverse transfer capacitance	Crss	_	49	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	42	_	ns	I <sub>D</sub> = 17.5 A
Rise time	t <sub>r</sub>	_	72	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	$t_{d(off)}$	_	162	_	ns	$R_L = 14.3 \Omega$
Fall time	t <sub>f</sub>	_	111	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	98	_	nC	V <sub>DD</sub> = 400 V
Gate to source charge	Qgs	_	17.6	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	42.3	_	nC	I <sub>D</sub> = 35 A
Body-drain diode forward voltage	$V_{DF}$	_	0.95	1.60	V	$I_F = 35 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	170	_	ns	$I_F = 35 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

#### **Package Dimensions**



### **Ordering Information**

Part No.	Quantity	Shipping Container
RJL5018DPK-00-T0	360 pcs	Box (Tube)

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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#### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510